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APPLICATION NO.: 10/020,004

ATTY. DOCKET NO.: H00498.70164.US

FILING DATE: December 11, 2001

CONFIRMATION NO.: 7232

APPLICANT:

Charles M. Lieber.

Sheet

GROUP ART UNIT: 2826 EXAMINER: Greene, Pershelle L.

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Conf. No.: 7232

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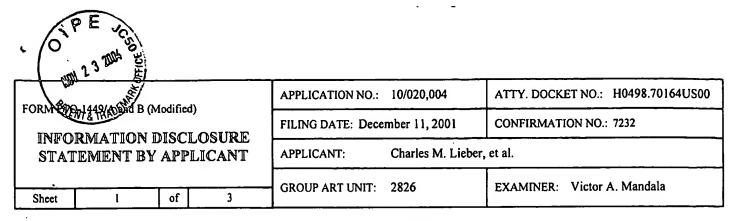
Serial No.: 10/020,004

Conf. No.: 7232

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APPLICATION NO.: 10/020,004 ATTY. DOCKET NO.: H0498.70164US00

FORMATION DISCLOSURE
STATEMENT BY APPLICANT

Sheet 2 of 3

APPLICATION NO.: 10/020,004 ATTY. DOCKET NO.: H0498.70164US00

FILING DATE: December 11, 2001 CONFIRMATION NO.: 7232

APPLICANT: Charles M. Lieber, et al.

GROUP ART UNIT: 2826 EXAMINER: Victor A. Mandala

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3 of Sheet 3

APPLICATION NO.: 10/020,004

ATTY. DOCKET NO.: H0498.70164US00

FILING DATE: December 11, 2001

**CONFIRMATION NO.: 7232** 

APPLICANT:

Charles M. Lieber, et al.

GROUP ART UNIT: 2826

EXAMINER: Victor A. Mandala

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STATEMENT BY APPLICANT			APPLICA	NT: Charles M. Lieber, et al.			
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